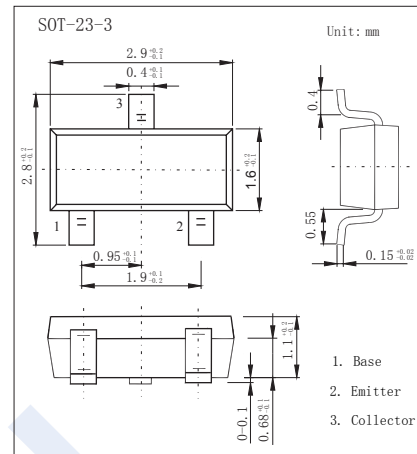


NPN Transistors

2SC5344SF

■ Features

- High h_{FE} : $h_{FE}=100\sim320$
- Complementary pair with 2SA1981SF



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	35	V
Collector - Emitter Voltage	V_{CE0}	30	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	800	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100\mu\text{A}$, $I_E = 0$	35			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 1\text{mA}$, $I_B = 0$	30			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100\mu\text{A}$, $I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 35\text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 1\text{V}$, $I_C = 100\text{mA}$	100		320	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		13		pF
Transition frequency	f_T	$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$		120		MHz

■ Classification of h_{FE}

Type	2SC5344SF-O	2SC5344SF-Y
Range	100-200	160-320
Marking	FAO	FAY

NPN Transistors 2SC5344SF

■ Typical Characteristics

Fig. 1 $P_C - T_a$

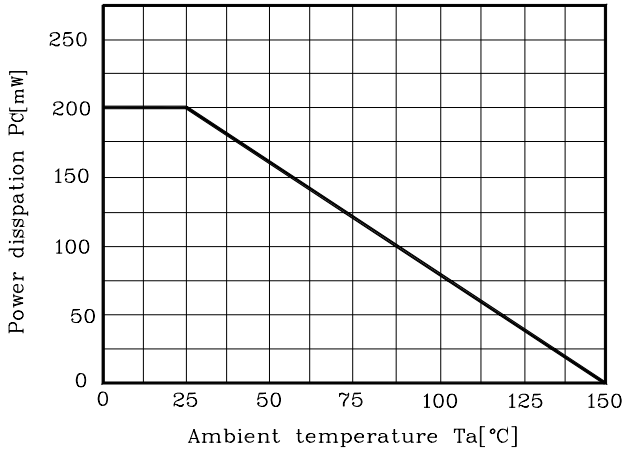


Fig. 2 $I_C - V_{BE}$

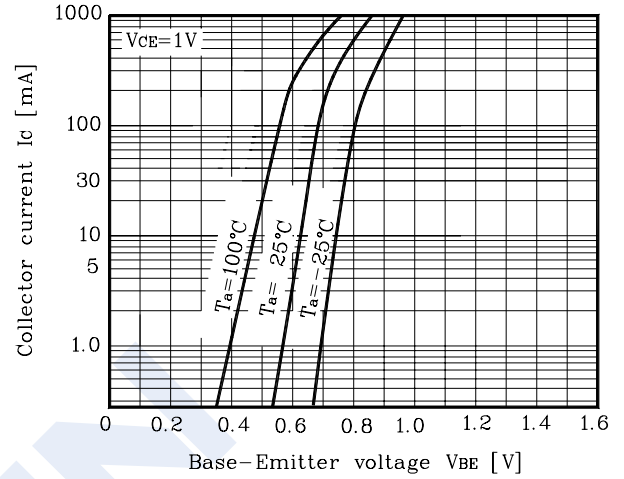


Fig. 3 $I_C - V_{CE}$

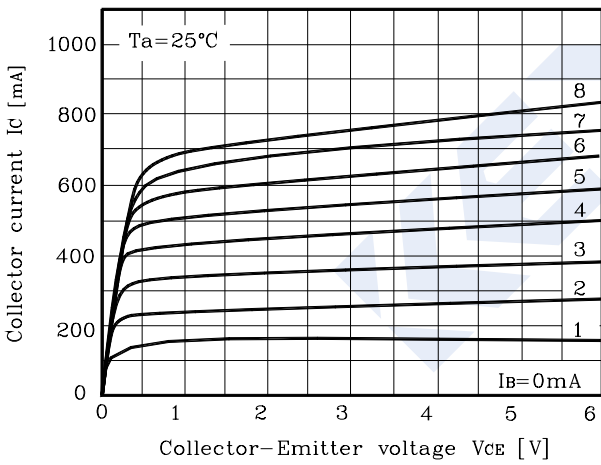


Fig. 4 $V_{CE(sat)} - I_C$

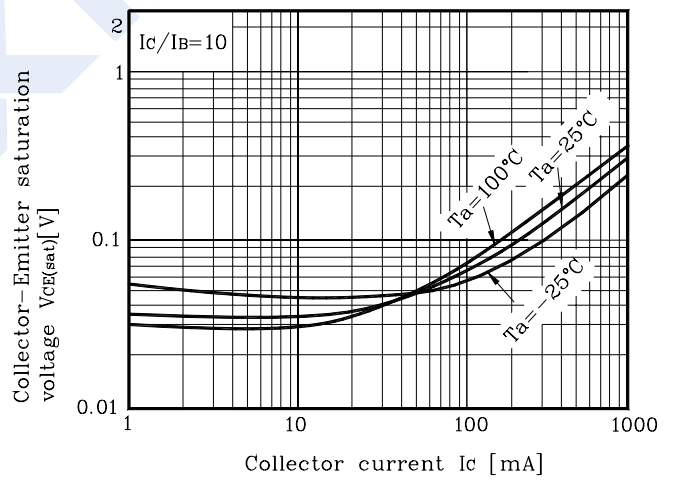


Fig. 5 $h_{FE} - I_C$

